TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

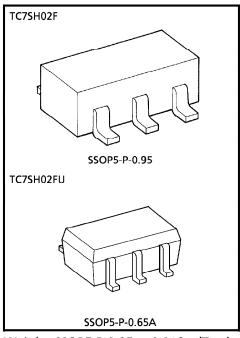
TC7SH02F, TC7SH02FU

2-INPUT NOR GATE

The TC7SH02 is an advanced high speed CMOS 2-INPUT NOR GATE fabricated with silicon gate C²MOS technology. It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation. The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output. An input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interfase 5V to 3V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

FEATURES

- High Speed ······ t_{pd} = 3.6ns (Typ.) at
- Low Power Dissipation $\cdots I_{CC} = 2\mu A$ (Max.) at
- High Noise Immunity ················ V_{NIH} = V_{NIL}
 = 28% V_{CC} (Min.)
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays ······· t_{pLH}≒t_{pHL}
- Wide Operating Voltage Range…… V_{CC (opr)} = 2~5.5V

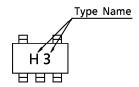


Weight SSOP5-P-0.95 : 0.016g (Typ.) SSOP5-P-0.65A : 0.006g (Typ.)

MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	Vcc	-0.5~7.0	V
DC Input Voltage	VIN	-0.5~7.0	V
DC Output Voltage	V _{OUT}	-0.5~V _{CC} +0.5	V
Input Diode Current	ΙΚ	- 20	mΑ
Output Diode Current	^I ок	± 20	mA
DC Output Current	IOUT	± 25	mΑ
DC V _{CC} /Ground Current	lcc	± 50	mA
Power Dissipation	PD	200	mW
Storage Temperature	T _{stg}	-65∼150	°C
Lead Temperature (10s)	TL	260	°C

MARKING



TRUTH TABLE

А	В	Y
L	L	Н
L	Н	L
Н	L	L
Н	Н	L

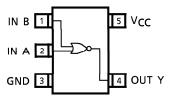
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LOGIC DIAGRAM



PIN ASSIGNMENT (TOP VIEW)



RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	Vcc	2.0~5.5	V
Input Voltage	VIN	0~5.5	V
Output Voltage	Vout	0~V _{CC}	V
Operating Temperature	T _{opr}	- 40∼85	°C
Input Rise and Fall Time	d /d	$0\sim100 \text{ (V}_{CC}=3.3\pm0.3\text{V)}$	ns /\/
	d _t /d _v	$0\sim 20 \ (V_{CC} = 5 \pm 0.5V)$	ns/V

DC ELECTRICAL CHARACTERISTICS

PARAMETER SYMBOL CIR		TEST	TEST CONDITION VCC			Ta = 25°C			Ta = − 40~85°C		LINUT
		CUIT			Vcc	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
High Lovel Indust					2.0	1.50	_	_	1.50	_	
High-Level Input Voltage	VIH	_	_		3.0~	VCC		_	Vcc		V
Voltage					5.5	×0.7		×0.7			
Low-Level Input			_		2.0	_	_	0.50	_	0.50	
Voltage	V _{IL}	_			3.0~	_	_	Vcc	_	VCC	
					5.5			×0.3		×0.3	
			V _{IN} = V _{IL}	I _{OH} = -50μA	2.0	1.9	2.0	-	1.9	—	_ v
High Level		_			3.0	2.9	3.0	—	2.9	_	
Output-Voltage	Voн				4.5	4.4	4.5		4.4	_	
Output-voitage				$I_{OH} = -4mA$	3.0	2.58	_	—	2.48	<u> </u>	
				$I_{OH} = -8mA$	4.5	3.94	_	—	3.80		
					2.0	-	0.0	0.1	_	0.1	
Low-Level Output-Voltage		_{\(\dots\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\}	$I_{OL} = 50 \mu A$	3.0	_	0.0	0.1	—	0.1		
	VOL	_	V _{IN} = V _{IH} or V _{IL}		4.5	-	0.0	0.1	_	0.1	V
				$I_{OL} = 4mA$	3.0	_	_	0.36	_	0.44	
				$I_{OL} = 8mA$	4.5	_	_	0.36	<u> </u>	0.44	
Input Leakage Current	IN	_	V _{IN} = 5.5V or GND		0~ 5.5		_	± 0.1	_	± 1.0	
Quiescent Supply Current	^l cc	_	V _{IN} = V _{CC} or GND		5.5			2.0		20.0	μΑ

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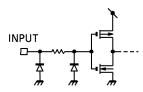
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AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3ns$)

PARAMETER SYMBOL	TEST	TEST CONDITION			Ta = 25°C			Ta = − 40~85°C		UNIT	
	CIR- CUIT		V _{CC} (V)	C _L (pF)	MIN.	TYP.	MAX.	MIN.	MAX.	OIVII	
Propagation tpLH Delay Time tpHL			_	3.3 ± 0.3 5.0 ± 0.5	15	_	5.6	7.9	1.0	9.5	ns
	t _{PLH}				50	_	8.1	11.4	1.0	13.0	
	tPHL	L —			15	_	3.6	5.5	1.0	6.5	
			3.0 ± 0.3	50	1	5.1	7.5	1.0	8.5		
Input Capacitance	C _{IN}	_	_			1	4	10	1	10	
Power Dissipation Capacitance	C _{PD}	_	Note (1)			_	15	_	_	_	pF

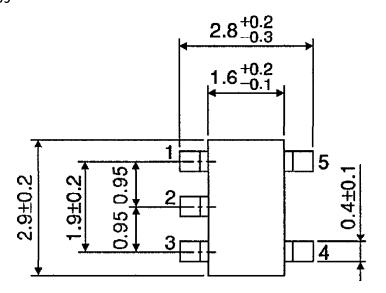
Note (1): CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation : ICC (opr) = CPD·VCC·fIN + ICC

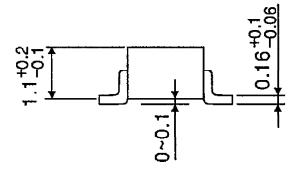
INPUT EQUIVALENT CIRCUIT



OUTLINE DRAWING SSOP5-P-0.95

Unit: mm

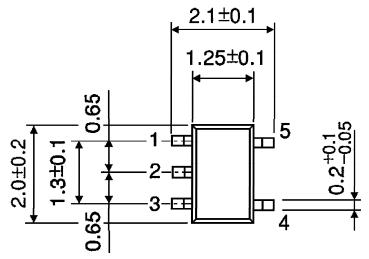




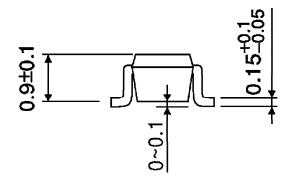
Weight: 0.016g (Typ.)

OUTLINE DRAWING

SSOP5-P-0.65A



Unit: mm



Weight: 0.006g (Typ.)